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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	154
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p600l-1pq208i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Device Overview

Low power flash devices consist of multiple distinct programmable architectural features (Figure 1-5 on page 13 through Figure 1-7 on page 14):

- FPGA fabric/core (VersaTiles)
- Routing and clock resources (VersaNets)
- FlashROM
- Dedicated SRAM and/or FIFO
 - 30 k gate and smaller device densities do not support SRAM or FIFO.
 - Automotive devices do not support FIFO operation.
- I/O structures
- Flash*Freeze technology and low power modes



Notes: * Bank 0 for the 30 k devices

† Flash*Freeze mode is supported on IGLOO devices.



Global Resources in Low Power Flash Devices

Figure 3-18 • Globals Management GUI in Designer

- 3. Occasionally, the synthesis tool assigns a global macro to clock nets, even though the fanout is significantly less than other asynchronous signals. Select **Demote global nets whose fanout is less than** and enter a reasonable value for fanouts. This frees up some global networks from the signals that have very low fanouts. This can also be done using PDC.
- 4. Use a local clock network for the signals that do not need to go to the whole chip but should have low skew. This local clock network assignment can only be done using PDC.
- 5. Assign the I/O buffer using MVN if you have fixed I/O assignment. As shown in Figure 3-10 on page 61, there are three sets of global pins that have a hardwired connection to each global network. Do not try to put multiple CLKBUF macros in these three sets of global pins. For example, do not assign two CLKBUFs to GAA0x and GAA2x pins.
- 6. You must click **Commit** at the end of MVN assignment. This runs the pre-layout checker and checks the validity of global assignment.
- 7. Always run Compile with the **Keep existing physical constraints** option on. This uses the quadrant clock network assignment in the MVN assignment and checks if you have the desired signals on the global networks.
- 8. Run Layout and check the timing.

SmartGen also allows the user to select the various delays and phase shift values necessary to adjust the phases between the reference clock (CLKA) and the derived clocks (GLA, GLB, GLC, YB, and YC). SmartGen allows the user to select the input clock source. SmartGen automatically instantiates the special macro, PLLINT, when needed.



Note: Clock divider and clock multiplier blocks are not shown in this figure or in SmartGen. They are automatically configured based on the user's required frequencies.

Figure 4-6 • CCC with PLL Block

Global Input Selections

Low power flash devices provide the flexibility of choosing one of the three global input pad locations available to connect to a CCC functional block or to a global / quadrant global network. Figure 4-7 on page 88 and Figure 4-8 on page 88 show the detailed architecture of each global input structure for 30 k gate devices and below, as well as 60 k gate devices and above, respectively. For 60 k gate devices and above (Figure 4-7 on page 88), if the single-ended I/O standard is chosen, there is flexibility to choose one of the global input pads (the first, second, and fourth input). Once chosen, the other I/O locations are used as regular I/Os. If the differential I/O standard is chosen (not applicable for IGLOO nano and ProASIC3 nano devices), the first and second inputs are considered as paired, and the third input is paired with a regular I/O.

The user then has the choice of selecting one of the two sets to be used as the clock input source to the CCC functional block. There is also the option to allow an internal clock signal to feed the global network or the CCC functional block. A multiplexer tree selects the appropriate global input for routing to the desired location. Note that the global I/O pads do not need to feed the global network; they can also be used as regular I/O pads.

compatible, which means devices can operate at conventional PCI frequencies (33 MHz and 66 MHz). PCI-X is more fault-tolerant than PCI. It also does not have programmable drive strength.

Voltage-Referenced Standards

I/Os using these standards are referenced to an external reference voltage (V_{REF}) and are supported on E devices only.

HSTL Class I and II (High-Speed Transceiver Logic)

These are general-purpose, high-speed 1.5 V bus standards (EIA/JESD 8-6) for signaling between integrated circuits. The signaling range is 0 V to 1.5 V, and signals can be either single-ended or differential. HSTL requires a differential amplifier input buffer and a push-pull output buffer. The reference voltage (VREF) is 0.75 V. These standards are used in the memory bus interface with data switching capability of up to 400 MHz. The other advantages of these standards are low power and fewer EMI concerns.

HSTL has four classes, of which low power flash devices support Class I and II. These classes are defined by standard EIA/JESD 8-6 from the Electronic Industries Alliance (EIA):

- Class I Unterminated or symmetrically parallel-terminated
- Class II Series-terminated
- Class III Asymmetrically parallel-terminated
- Class IV Asymmetrically double-parallel-terminated

SSTL2 Class I and II (Stub Series Terminated Logic 2.5 V)

These are general-purpose 2.5 V memory bus standards (JESD 8-9) for driving transmission lines, designed specifically for driving the DDR SDRAM modules used in computer memory. SSTL2 requires a differential amplifier input buffer and a push-pull output buffer. The reference voltage (VREF) is 1.25 V.

SSTL3 Class I and II (Stub Series Terminated Logic 3.3 V)

These are general-purpose 3.3 V memory bus standards (JESD 8-8) for driving transmission lines. SSTL3 requires a differential amplifier input buffer and a push-pull output buffer. The reference voltage (VREF) is 1.5 V.



Figure 7-6 • SSTL and HSTL Topology

GTL 2.5 V (Gunning Transceiver Logic 2.5 V)

This is a low power standard (JESD 8.3) for electrical signals used in CMOS circuits that allows for low electromagnetic interference at high transfer speeds. It has a voltage swing between 0.4 V and 1.2 V and typically operates at speeds of between 20 and 40 MHz. VCCI must be connected to 2.5 V. The reference voltage (VREF) is 0.8 V.

GTL 3.3 V (Gunning Transceiver Logic 3.3 V)

This is the same as GTL 2.5 V above, except VCCI must be connected to 3.3 V.

IGLOO and ProASIC3

For boards and cards with three levels of staging, card power supplies must have time to reach their final values before the I/Os are connected. Pay attention to the sizing of power supply decoupling capacitors on the card to ensure that the power supplies are not overloaded with capacitance.

Cards with three levels of staging should have the following sequence:

- Grounds
- Powers
- I/Os and other pins

For Level 3 and Level 4 compliance with the 30K gate device, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 μ s.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 7-12 on page 193). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30K gate devices do not have built-in I/O clamp diodes.

For other IGLOO and ProASIC3 devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 k Ω , and the resulting current is equal to 3.3 V / 45 k Ω = 73 µA for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input LOW when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

Selectable Skew between Output Buffer Enable and Disable Times

Low power flash devices have a configurable skew block in the output buffer circuitry that can be enabled to delay output buffer assertion without affecting deassertion time. Since this skew block is only available for the OE signal, the feature can be used in tristate and bidirectional buffers. A typical 1.2 ns delay is added to the OE signal to prevent potential bus contention. Refer to the appropriate family datasheet for detailed timing diagrams and descriptions.

The skew feature is available for all I/O standards.

This feature can be implemented by using a PDC command (Table 7-5 on page 179) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

The configurable skew block is used to delay output buffer assertion (enable) without affecting deassertion (disable) time.



Figure 7-13 • Block Diagram of Output Enable Path





ProASIC3L FPGA Fabric User's Guide







Figure 7-18 • Timing Diagram (with skew circuit selected)

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I/O Structures in IGLOO and ProASIC3 Devices

Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout

Each I/O voltage bank has a separate ground and power plane for input and output circuits (VMV/GNDQ for input buffers and VCCI/GND for output buffers). This isolation is necessary to minimize simultaneous switching noise from the input and output (SSI and SSO). The switching noise (ground bounce and power bounce) is generated by the output buffers and transferred into input buffer circuits, and vice versa.

Since voltage bounce originates on the package inductance, the VMV and VCCI supplies have separate package pin assignments. For the same reason, GND and GNDQ also have separate pin assignments.

The VMV and VCCI pins must be shorted to each other on the board. Also, the GND and GNDQ pins must be shorted to each other on the board. This will prevent unwanted current draw from the power supply.

SSOs can cause signal integrity problems on adjacent signals that are not part of the SSO bus. Both inductive and capacitive coupling parasitics of bond wires inside packages and of traces on PCBs will transfer noise from SSO busses onto signals adjacent to those busses. Additionally, SSOs can produce ground bounce noise and VCCI dip noise. These two noise types are caused by rapidly changing currents through GND and VCCI package pin inductances during switching activities (EQ 2 and EQ 3).

Ground bounce noise voltage = L(GND) × di/dt

VCCI dip noise voltage = L(VCCI) × di/dt

EQ 3

EQ 2

Any group of four or more input pins switching on the same clock edge is considered an SSO bus. The shielding should be done both on the board and inside the package unless otherwise described.

In-package shielding can be achieved in several ways; the required shielding will vary depending on whether pins next to the SSO bus are LVTTL/LVCMOS inputs, LVTTL/LVCMOS outputs, or GTL/SSTL/HSTL/LVDS/LVPECL inputs and outputs. Board traces in the vicinity of the SSO bus have to be adequately shielded from mutual coupling and inductive noise that can be generated by the SSO bus. Also, noise generated by the SSO bus needs to be reduced inside the package.

PCBs perform an important function in feeding stable supply voltages to the IC and, at the same time, maintaining signal integrity between devices.

Key issues that need to be considered are as follows:

- · Power and ground plane design and decoupling network design
- Transmission line reflections and terminations

For extensive data per package on the SSO and PCB issues, refer to the "ProASIC3/E SSO and Pin Placement and Guidelines" chapter of the *ProASIC3 FPGA Fabric User's Guide*.

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I/O Structures in IGLOO and ProASIC3 Devices

Related Documents

Application Notes

Board-Level Considerations http://www.microsemi.com/soc/documents/ALL_AC276_AN.pdf

User's Guides

Libero SoC User's Guide http://www.microsemi.com.soc/documents/libero_ug.pdf IGLOO, Fusion, and ProASIC3 Macro Library Guide http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf SmartGen Core Reference Guide http://www.microsemi.com/soc/documents/genguide_ug.pdf

List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Change	Page
August 2012	Figure 7-1 • DDR Configured I/O Block Logical Representation and Figure 7-2 • DDR Configured I/O Block Logical Representation were revised to indicate that resets on registers 1, 3, 4, and 5 are active high rather than active low. The title of the figures was revised from "I/O Block Logical Representation" (SAR 38215).	175, 181
	AGL015 and A3P015 were added to Table 7-2 • Supported I/O Standards. 1.2 V was added under single-ended I/O standards. LVCMOS 1.2 was added to Table 7-3 • VCCI Voltages and Compatible IGLOO and ProASIC3 Standards (SAR 38096).	177
	Figure 7-4 • Simplified I/O Buffer Circuitry and Table 7-7 • Programmable I/O Features (user control via I/O Attribute Editor) were modified to indicate that programmable input delay control is applicable only to ProASIC3EL and RT ProASIC3 devices (SAR 39666).	183, 188
	The following sentence is incorrect and was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 40191):	184
	other devices there is no clamp diode.	
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663).	208, 210
June 2011	Figure 7-1 • DDR Configured I/O Block Logical Representation and Figure 7-2 • DDR Configured I/O Block Logical Representation were revised so that the I/O_CLR and I/O_OCLK nets are no longer joined in front of Input Register 3 but instead on the branch of the CLR/PRE signal (SAR 26052).	175, 181
	Table 7-1 • Flash-Based FPGAs was revised to remove RT ProASIC3 and addMilitary ProASIC3/EL in its place (SAR 31824, 31825).	176
	The "Advanced I/Os—IGLOO, ProASIC3L, and ProASIC3" section was revised. Formerly it stated, "3.3 V PCI and 3.3 V PCI-X are 5 V–tolerant." This sentence now reads, "3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V–tolerant" (SAR 20983).	177

I/O Structures in IGLOOe and ProASIC3E Devices

I/O Architecture

I/O Tile

The I/O tile provides a flexible, programmable structure for implementing a large number of I/O standards. In addition, the registers available in the I/O tile can be used to support high-performance register inputs and outputs, with register enable if desired (Figure 8-3). The registers can also be used to support the JESD-79C Double Data Rate (DDR) standard within the I/O structure (see the "DDR for Microsemi's Low Power Flash Devices" section on page 271 for more information).

As depicted in Figure 8-3, all I/O registers share one CLR port. The output register and output enable register share one CLK port.



Figure 8-3 • DDR Configured I/O Block Logical Representation



I/O Structures in IGLOOe and ProASIC3E Devices

Solution 3

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the bus switch, as shown in Figure 8-12. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.



Figure 8-12 • Solution 3

Power-Up Behavior

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

Drive Strength

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF_S_12 (slew = low, out_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 232). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

	Clock			I/O			
Interface	Туре	Frequency	Туре	Signals In	Signals Out	Data I/O	
GM	Src Sync	125 MHz	LVTTL	8	8	125 Mbps	
ТВІ	Src Sync	125 MHz	LVTTL	10	10	125 Mbps	
XSBI	Src Sync	644 MHz	LVDS	16	16	644 Mbps	
XGMI	Src Sync DDR	156 MHz	HSTL1	32	32	312 Mbps	
FlexBus 3	Sys Sync	104 MHz	LVTTL	≤ 32	≤ 32	≤ 104	
Pos-PHY3/SPI-3	Sys Sync	104	LVTTL	8,16,32	8,16,32	\leq 104 Mbps	
FlexBus 4/SPI-4.1	Src Sync	200 MHz	HSTL1	16,64	16,64	200 Mbps	
Pos-PHY4/SPI-4.2	Src Sync DDR	≥ 311 MHz	LVDS	16	16	\geq 622 Mbps	
SFI-4.1	Src Sync	622 MHz	LVDS	16	16	622 Mbps	
CSIX L1	Sys Sync	\leq 250 MHz	HSTL1	32,64,96,128	32,64,96,128	\leq 250 Mbps	
Hyper Transport	Sys Sync DDR	\leq 800 MHz	LVDS	2,4,8,16	2,4,8,16	\leq 1.6 Gbps	
Rapid I/O Parallel	Sys Sync DDR	250 MHz – 1 GHz	LVDS	8,16	8,16	\leq 2 Gbps	
Star Fabric	CDR		LVDS	4	4	622 Mbps	

Table 8-19 • High-Level Interface Examples

Note: Sys Sync = System Synchronous Clocking, Src Sync = Source Synchronous Clocking, and CDR = Clock and Data Recovery.



DDR for Microsemi's Low Power Flash Devices

Table 10-2 • DDR I/O Options (continued)

DDR Register	I/O Type	I/O Standard	Sub-Ontions	Comments	
Transmit Register	Tristate	Normal	Enable Polarity	Low/bigb (low default)	
(continued)	Buffer	LVTTL	Output Drive	2, 4, 6, 8, 12,16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)	
			Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		PCI/PCI-X	Enable Polarity	Low/high (low default)	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)	
			Enable Polarity	Low/high (low default)	
		HSTL	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
		SSTL2/SSTL3	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
	Bidirectional Buffer	Normal	Enable Polarity	Low/high (low default)	
		LVTTL	Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)	
			Slew Rate	Low/high (high default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up/-Down	None (default)	
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)	
			Enable Polarity	Low/high (low default)	
			Pull-Up	None (default)	
		PCI/PCI-X	None		
			Enable Polarity	Low/high (low default)	
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)	
			Enable Polarity	Low/high (low default)	
		HSTL	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	
		SSTL2/SSTL3	Class	I / II (I default)	
			Enable Polarity	Low/high (low default)	

Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.

Figure 10-11 • DDR Input/Output Cells as Seen by ChipPlanner for IGLOO/e Devices

Verilog

module Inbuf_ddr(PAD,CLR,CLK,QR,QF);

input PAD, CLR, CLK; output QR, QF;

wire Y;

```
DDR_REG_DDR_REG_0_inst(.D(Y), .CLK(CLK), .CLR(CLR), .QR(QR), .QF(QF));
INBUF INBUF_0_inst(.PAD(PAD), .Y(Y));
```

endmodule

module Outbuf_ddr(DataR,DataF,CLR,CLK,PAD);

input DataR, DataF, CLR, CLK; output PAD;

wire Q, VCC;

```
VCC VCC_1_net(.Y(VCC));
DDR_OUT DDR_OUT_0_inst(.DR(DataR), .DF(DataF), .CLK(CLK), .CLR(CLR), .Q(Q));
OUTBUF OUTBUF_0_inst(.D(Q), .PAD(PAD));
```

endmodule



Security in Low Power Flash Devices

The AES key is securely stored on-chip in dedicated low power flash device flash memory and cannot be read out. In the first step, the AES key is generated and programmed into the device (for example, at a secure or trusted programming site). The Microsemi Designer software tool provides AES key generation capability. After the key has been programmed into the device, the device will only correctly decrypt programming files that have been encrypted with the same key. If the individual programming file content is incorrect, a Message Authentication Control (MAC) mechanism inside the device will fail in authenticating the programming file. In other words, when an encrypted programming file is being loaded into a device that has a different programmed AES key, the MAC will prevent this incorrect data from being loaded, preventing possible device damage. See Figure 12-3 on page 304 and Figure 12-4 on page 306 for graphical representations of this process.

It is important to note that the user decides what level of protection will be implemented for the device. When AES protection is desired, the FlashLock Pass Key must be set. The AES key is a content protection mechanism, whereas the FlashLock Pass Key is a device protection mechanism. When the AES key is programmed into the device, the device still needs the Pass Key to protect the FPGA and FlashROM contents and the security settings, including the AES key. Using the FlashLock Pass Key prevents modification of the design contents by means of simply programming the device with a different AES key.

AES Decryption and MAC Authentication

Low power flash devices have a built-in 128-bit AES decryption core, which decrypts the encrypted programming file and performs a MAC check that authenticates the file prior to programming.

MAC authenticates the entire programming data stream. After AES decryption, the MAC checks the data to make sure it is valid programming data for the device. This can be done while the device is still operating. If the MAC validates the file, the device will be erased and programmed. If the MAC fails to validate, then the device will continue to operate uninterrupted.

This will ensure the following:

- · Correct decryption of the encrypted programming file
- Prevention of erroneous or corrupted data being programmed during the programming file transfer
- Correct bitstream passed to the device for decryption



Figure 12-4 • Example Application Scenario Using AES in IGLOO and ProASIC3 Devices

1. National Institute of Standards and Technology, "ADVANCED ENCRYPTION STANDARD (AES) Questions and Answers," 28 January 2002 (10 January 2005). See http://csrc.nist.gov/archive/aes/index1.html for more information.



In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X

signal deactivated, which also has the effect of disabling the input buffers. The SAMPLE/PRELOAD instruction captures the status of pads in parallel and shifts them out as new data is shifted in for loading into the Boundary Scan Register (BSR). When the device is in an unprogrammed state, the OE and output BSR will be undefined; however, the input BSR will be defined as long as it is connected and being used. For JTAG timing information on setup, hold, and fall times, refer to the *FlashPro User's Guide*.

ISP Support in Flash-Based Devices

The flash FPGAs listed in Table 13-1 support the ISP feature and the functions described in this document.

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
SmartFusion	SmartFusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable microcontroller subsystem (MSS) which includes programmable analog and an ARM® Cortex [™] -M3 hard processor and flash memory in a monolithic device
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex™-M1 soft processors, and flash memory into a monolithic device
ProASIC	ProASIC	First generation ProASIC devices
	ProASIC ^{PLUS}	Second generation ProASIC devices

Table 13-1 • Flash-Based FPGAs Supporting ISP

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 13-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 13-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

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Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming

3. VCC switches from 1.5 V to 1.2 V when TRST is LOW.

Figure 14-4 • TRST Toggled LOW

In Figure 14-4, the TRST signal and the VCC core voltage signal are labeled. As TRST is pulled to ground, the core voltage is observed to switch from 1.5 V to 1.2 V. The observed fall time is approximately 2 ms.

DirectC

The above analysis is based on FlashPro3, but there are other solutions to ISP, such as DirectC. DirectC is a microprocessor program that can be run in-system to program Microsemi flash devices. For FlashPro3, TRST is the most convenient control signal to use for the recommended circuit. However, for DirectC, users may use any signal to control the FET. For example, the DirectC code can be edited so that a separate non-JTAG signal can be asserted from the microcontroller that signals the board that it is about to start programming the device. After asserting the N-Channel Digital FET control signal, the programming algorithm must allow sufficient time for the supply to rise to 1.5 V before initiating DirectC programming. As seen in Figure 14-3 on page 345, 50 ms is adequate time. Depending on the size of the PCB and the capacitance on the VCC supply, results may vary from system to system. Microsemi recommends using a conservative value for the wait time to make sure that the VCC core voltage is at the right level.

Conclusion

For applications using IGLOO and ProASIC3L low power FPGAs and taking advantage of the low core voltage power supplies with less than 1.5 V operation, there must be a way for the core voltage to switch from 1.2 V (or other voltage) to 1.5 V, which is required during in-system programming. The circuit explained in this document illustrates one simple, cost-effective way of handling this requirement. A JTAG signal from the FlashPro3 programmer allows the circuit to sense when programming is in progress, enabling it to switch to the correct core voltage.



useless to the thief. To learn more about the low power flash devices' security features, refer to the "Security in Low Power Flash Devices" section on page 301.

Figure 15-5 • ProASIC3 Device Encryption Flow

Conclusion

The Fusion, IGLOO, and ProASIC3 FPGAs are ideal for applications that require field upgrades. The single-chip devices save board space by eliminating the need for EEPROM. The built-in AES with MAC enables transmission of programming data over any network without fear of design theft. Fusion, IGLOO, and ProASIC3 FPGAs are IEEE 1532–compliant and support STAPL, making the target programming software easy to implement.

Microsemi

UJTAG Applications in Microsemi's Low Power Flash Devices



Figure 17-3 • Connectivity Method of UJTAG Macro

UJTAG Operation

There are a few basic functions of the UJTAG macro that users must understand before designing with it. The most important fundamental concept of the UJTAG design is its connection with the TAP Controller state machine.

TAP Controller State Machine

The 16 states of the TAP Controller state machine are shown in Figure 17-4 on page 367. The 1s and 0s, shown adjacent to the state transitions, represent the TMS values that must be present at the time of a rising TCK edge for a state transition to occur. In the states that include the letters "IR," the instruction register operates; in the states that contain the letters "DR," the test data register operates. The TAP Controller receives two control inputs, TMS and TCK, and generates control and clock signals for the rest of the test logic.

On power-up (or the assertion of TRST), the TAP Controller enters the Test-Logic-Reset state. To reset the controller from any other state, TMS must be held HIGH for at least five TCK cycles. After reset, the TAP state changes at the rising edge of TCK, based on the value of TMS.



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